

25C D ■ 8235605 0004554 0 ■ SIEG T-31-17

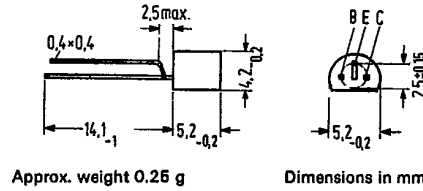
PNP Silicon Planar Transistor

BF 926

SIEMENS AKTIENGESELLSCHAFT 04554 D

BF 926 is an epitaxial PNP silicon planar transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is intended for use in VHF oscillator stages, in particular for driving MOS mixer stages.

Type	Ordering code
BF 926	Q62702-F 678



Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	40	V
Emitter-base voltage	$-V_{EBO}$	4	V
Collector current	$-I_C$	25	mA
Emitter current	$-I_E$	30	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Total power dissipation ($T_{amb} = 45^\circ\text{C}$)	P_{tot}	300	mW

Thermal resistance

Junction to ambient air	R_{thJA}	<350	K/W
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Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Collector cutoff current ($-V_{CB} = 20\text{ V}$)	$-I_{CBO}$	< 60	nA
Collector-emitter breakdown voltage ($-I_C = 2\text{ mA}$)	$-V_{CEO}$	> 30	V
Collector-base breakdown voltage ($-I_C = 10\text{ }\mu\text{A}$)	$-V_{CBO}$	> 40	V
Emitter-base breakdown voltage ($-I_E = 10\text{ }\mu\text{A}$)	$-V_{EBO}$	> 4	V
DC current gain ($-I_C = 1\text{ mA}$; $-V_{CE} = 10\text{ V}$)	h_{FE}	80 (> 30)	-

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Transition frequency ($-I_C = 5\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$)	f_T	600	MHz
Reverse transfer capacitance ($-V_{CB} = 10\text{ V}$; $-I_C = 5\text{ mA}$; $f = 1\text{ MHz}$)	$-C_{12e}$	0.6	pF
Output capacitance ($-I_E = 0$; $-V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$)	C_{OB}	0.8	pF
Input capacitance ($-V_{EBO} = 0.15\text{ V}$; $NF = 1\text{ MHz}$)	C_{EBO}	2	pF